

TC7S02F, TC7S02FU

2-INPUT NOR GATE

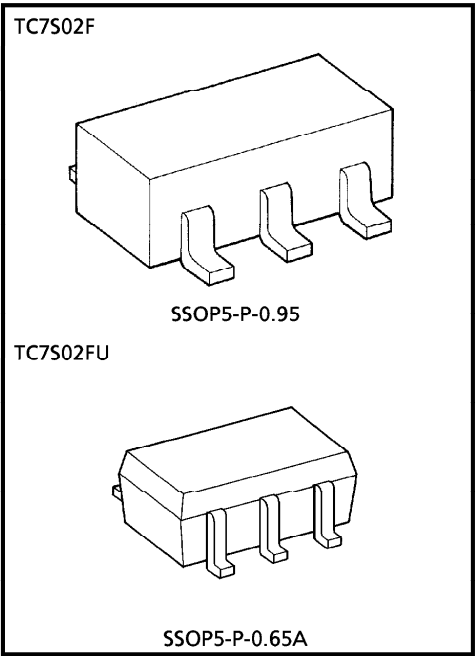
The TC7S02 is a high speed C<sup>2</sup>MOS 2-INPUT NOR GATE fabricated with silicon gate C<sup>2</sup>MOS technology. It achieves high speed operation similar to equivalent LSTTL while maintaining the C<sup>2</sup>MOS low power dissipation. The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage. Output currents are 1/2 compared to TC74HC series models.

FEATURES

- High Speed .....  $t_{pd} = 7ns$  (Typ.) at  $V_{CC} = 5V$
- Low Power Dissipation .....  $I_{CC} = 1\mu A$  (Max.) at  $T_a = 25^{\circ}C$
- High Noise Immunity .....  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Output Drive Capability ..... 5 LSTTL Loads
- Symmetrical Output Impedance ...  $|I_{OH}| = I_{OL} = 2mA$  (Min.)
- Balanced Propagation Delays .....  $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range ...  $V_{CC} (opr) = 2 \sim 6V$

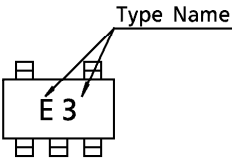
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	$V_{CC}$	$-0.5 \sim 7$	V
DC Input Voltage	$V_{IN}$	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	$\pm 20$	mA
Output Diode Current	$I_{OK}$	$\pm 20$	mA
DC Output Current	$I_{OUT}$	$\pm 12.5$	mA
DC $V_{CC}$ / Ground Current	$I_{CC}$	$\pm 25$	mA
Power Dissipation	$P_D$	200	mW
Storage Temperature	$T_{stg}$	$-65 \sim 150$	$^{\circ}C$
Lead Temperature (10s)	$T_L$	260	$^{\circ}C$

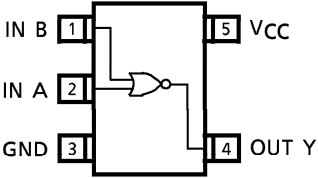


Weight SSOP5-P-0.95 : 0.016g (Typ.)  
SSOP5-P-0.65A : 0.006g (Typ.)

MARKING



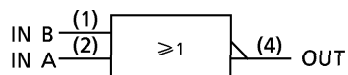
PIN ASSIGNMENT (TOP VIEW)



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## LOGIC DIAGRAM



## RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	$V_{CC}$	2~6	V
Input Voltage	$V_{IN}$	0~ $V_{CC}$	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$t_r, t_f$	0~1000 ( $V_{CC} = 2.0V$ ) 0~500 ( $V_{CC} = 4.5V$ ) 0~400 ( $V_{CC} = 6.0V$ )	ns

## DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	$T_a = 25^\circ C$				$T_a = -40 \sim 85^\circ C$		UNIT
			$V_{CC}$	MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Input Voltage	$V_{IH}$	—	2.0 4.5 6.0	1.5 3.15 4.2	— — —	— — —	1.5 3.15 4.2	— — —	V
Low-Level Input Voltage	$V_{IL}$	—	2.0 4.5 6.0	— — —	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	V
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IL}$ $I_{OH} = -20\mu A$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	— — —	V
			4.5 6.0	4.18 5.80	4.31 5.80	— —	4.13 5.63	— —	
			—	—	—	—	—	—	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 20\mu A$	2.0 4.5 6.0	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
			4.5 6.0	— —	0.17 0.18	0.26 0.26	— —	0.33 0.33	
			—	—	—	—	—	—	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	6.0	—	—	$\pm 0.1$	—	$\pm 1.0$	$\mu A$
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	

Output currents are 1/2 compared to TC74HC series models.

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AC ELECTRICAL CHARACTERISTICS (CL = 15pF, Input tr = tf = 6ns, VCC = 5V)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
			MIN.	TYP.	MAX.	
Output Transition Time	tTLH tTHL	—	—	5	10	ns
Propagation Delay Time	tPLH tPHL	—	—	7	15	ns

AC ELECTRICAL CHARACTERISTICS (CL = 50pF, Input tr = tf = 6ns)

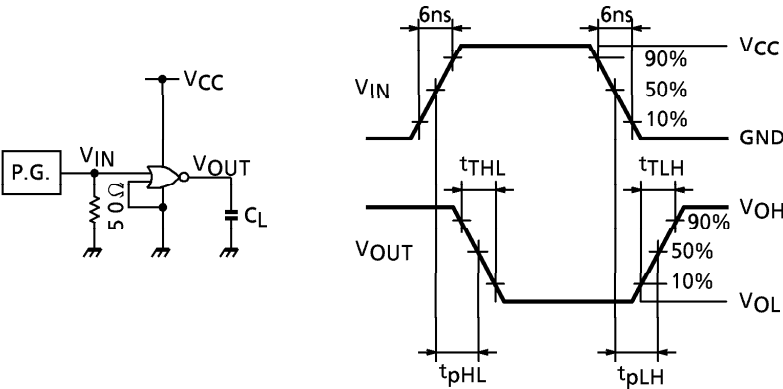
CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT
			VCC	MIN.	TYP.	MAX.	MIN.	MAX.
Output Transition Time	tTLH tTHL	—	2.0	—	50	125	—	155
			4.5	—	14	25	—	31
			6.0	—	12	21	—	26
Propagation Delay Time	tPLH tPHL	—	2.0	—	48	100	—	125
			4.5	—	12	20	—	25
			6.0	—	9	17	—	21
Input Capacitance	CIN	—	—	5	10	—	10	pF
Power Dissipation Capacitance	CPD	(Note 1)	—	10	—	—	—	

Note 1 : CPD defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

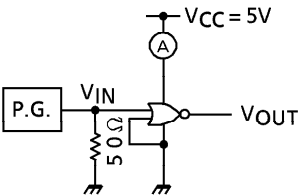
Average operating current can be obtained by the equation hereunder.

ICC (opr) = CPD · VCC · fIN + ICC

SWITCHING CHARACTERISTICS TEST CIRCUIT



ICC (opr) TEST CIRCUIT



Input waveform is the same as that in case of switching characteristics test.